

Silicon NPN Power Transistors

2SC1447

DESCRIPTION

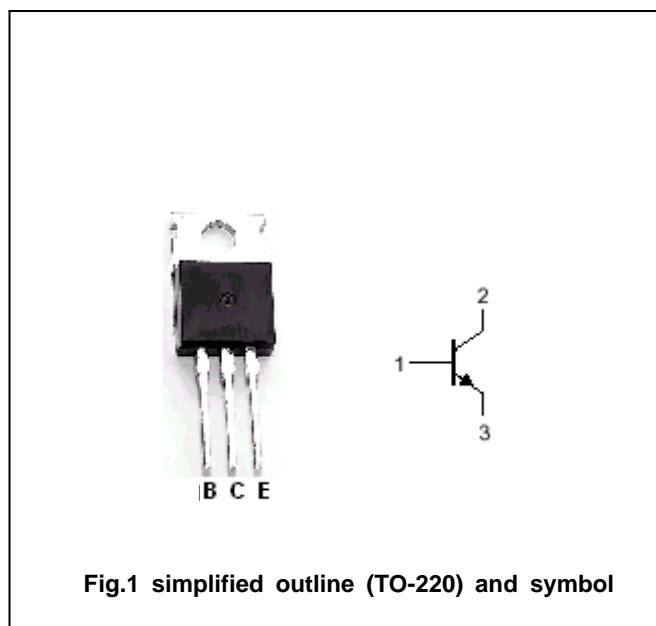
- With TO-220 package
- High breakdown voltage
- High transition frequency

APPLICATIONS

- For color TV chroma output applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |



Absolute maximum ratings (Ta=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | 300 | V |
| V _{CEO} | Collector-emitter voltage | Open base | 300 | V |
| V _{EBO} | Emitter-base voltage | Open collector | 7 | V |
| I _C | Collector current | | 0.15 | A |
| P _C | Collector power dissipation | T _C =25°C | 20 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =10 μ A ; I _E =0 | 300 | | | V |
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =10mA ; I _B =0 | 300 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =10 μ A ; I _C =0 | 7 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =50mA ; I _B =5mA | | | 2.0 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =250V ; I _E =0 | | | 1.0 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =5V ; I _C =0 | | | 1.0 | μ A |
| h _{FE} | DC current gain | I _C =50mA ; V _{CE} =10V | 40 | | 170 | |
| f _T | Transition frequency | I _C =10mA ; V _{CE} =30V | | 80 | | MHz |

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PACKAGE OUTLINE

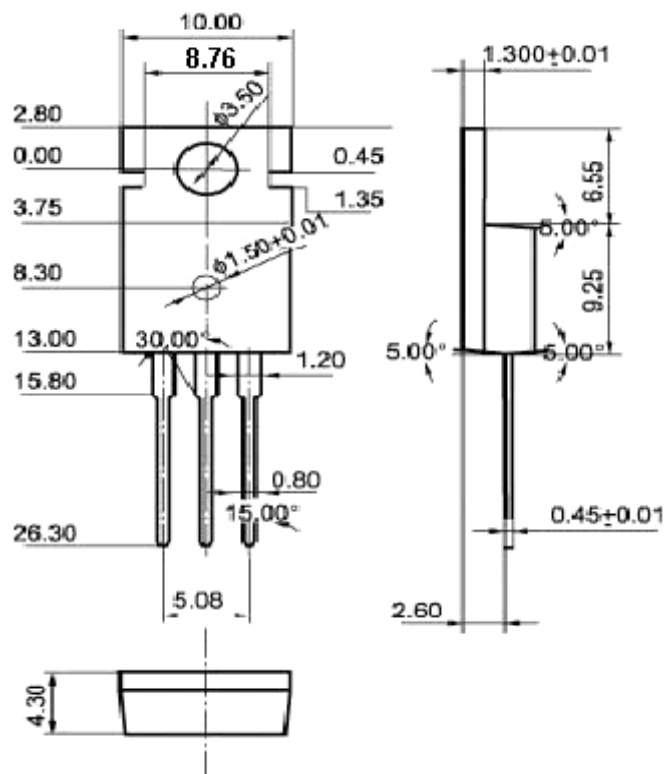


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)